

Appl. No. : 09/828,550
Filed : April 6, 2001

AMENDMENTS TO THE CLAIMS

Amendments to the Claims:

Please amend Claim 1 and cancel Claim 5 as indicated below. The below listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. **(Currently amended)** A semiconductor processing apparatus comprising a reaction chamber and one or more vitreous components that have a support surface for supporting other components in the reaction chamber, said support surface being covered at least in part by a devitrification barrier coating that is bonded to said support surface and directly contacts said supported other components in the reaction chamber; where said devitrification barrier coating has a thickness between about 1 and 10,000 angstroms.

2. **(Original)** The apparatus of Claim 1, wherein said one or more vitreous components are formed from quartz.

3. **(Original)** The apparatus of Claim 1, wherein said devitrification barrier comprises silicon nitride.

4. **(Original)** The apparatus of Claim 1, wherein said devitrification barrier coating is formed from silicon nitride that has been deposited on said one or more vitreous components using CVD deposition.

5. **(Canceled)**

6. **(Currently amended)** The apparatus of Claim 1 ~~5~~, where said devitrification barrier coating has a thickness between about 50 and 5000 angstroms ~~thick~~.

7. **(Previously presented)** The apparatus of Claim 6, where said devitrification barrier coating has a thickness between about 500 and 3,000 angstroms.

8. **(Previously presented)** The apparatus of Claim 7, where said devitrification barrier coating has a thickness of about 800 angstroms.

9. **(Previously presented)** The apparatus of Claim 1, where said devitrification barrier coating is selected from the group consisting of silicon nitride, diamond, titanium nitride, titanium carbon nitride, and combinations thereof.

10. **(Previously presented)** The apparatus of Claim 1, wherein said devitrification barrier coating covers an entire portion of said support surface of said one or more vitreous components.

11. **(Canceled)**

12. **(Canceled)**

13. **(Previously presented)** The apparatus of Claim 1, wherein said apparatus further comprises a support device comprising at least one laterally extending member, said radially extending member including an upwardly extending projection that defines said support surface, said projection and support device configured to support a substrate within said apparatus, said support surface of said projection being covered at least in part by said devitrification barrier coating.

14. **(Original)** The apparatus of Claim 1, wherein said reaction chamber is a chemical vapor deposition reaction chamber.

15. **(Withdrawn)** A thermocouple configured for use in a chemical vapor deposition process chamber, said thermocouple comprising:

thermocouple wires;

a vitreous sheath surrounding the wires; and

a devitrification barrier coating covering at least a portion of said sheath.

16. **(Withdrawn)** The thermocouple of Claim 15, wherein said vitreous sheath is formed from quartz.

17. **(Withdrawn)** The thermocouple of Claim 16, wherein said devitrification barrier coating comprises silicon nitride.

18. **(Withdrawn)** The thermocouple of Claim 15, where said devitrification barrier coating has a thickness between about 1 and 10,000 angstroms.

19. **(Withdrawn)** The thermocouple of Claim 18, where said devitrification barrier coating has a thickness between about 50 and 5000 angstroms thick.

20. **(Withdrawn)** The thermocouple of Claim 19, where said devitrification barrier coating has a thickness between about 500 and 3,000 angstroms thick.

21. **(Withdrawn)** The thermocouple of Claim 15, where said devitrification barrier coating is formed from the group consisting silicon nitride, diamond, titanium nitride, titanium carbon nitride and combinations thereof.

22. **(Withdrawn)** The thermocouple of Claim 15, wherein said devitrification barrier coating covers an entire portion of said thermocouple.

23. **(Withdrawn)** The thermocouple of Claim 15, wherein devitrification barrier coating covers a portion of the thermocouple that is most susceptible to devitrification.

24. **(Withdrawn)** The thermocouple of Claim 15, wherein devitrification barrier coating covers a tip of said thermocouple.

25. **(Withdrawn)** A method of minimizing divitrification in one or more vitreous components of a chemical vapor deposition process chamber, said method comprising the step of coating at least a portion of said one or more vitreous components with a barrier layer to protect said one or more vitreous components from processing gases in the chemical vapor deposition process chamber.

26. **(Withdrawn)** The method of Claim 25, wherein coating at least a portion of said one or more vitreous components with a barrier layer includes using chemical vapor deposition to form said barrier layer.

27. **(Withdrawn)** The method of Claim 25, wherein coating at least a portion of said one or more vitreous components includes forming the barrier layer from silicon nitride .

28. **(Withdrawn)** The method of Claim 27, wherein said step of forming the barrier layer out of silicon nitride includes using chemical vapor deposition to form said barrier layer.

29. **(Withdrawn)** The method of Claim 27, wherein said step of forming the barrier layer out of silicon nitride includes forming said barrier layer such that said barrier layer has a thickness between about 1 and 10,000 angstroms.

30. **(Withdrawn)** The method of Claim 29, wherein said step of forming the barrier layer out of silicon nitride includes forming said barrier layer such that said barrier layer has a thickness between about 500 and 3,000 angstroms thick.

31. **(Withdrawn)** The method of Claim 25, wherein coating at least a portion of said one or more vitreous components with a barrier layer includes forming the barrier layer from the group consisting of silicon nitride, diamond, titanium nitride, titanium carbon nitride, and combinations thereof.

32. **(Withdrawn)** The method of Claim 25, wherein coating at least a portion of said one or more vitreous components includes coating at least a portion of a thermocouple sheath.

33. **(Withdrawn)** The method of Claim 32, wherein coating at least a portion of said thermocouple includes coating a portion of the thermocouple sheath that is most susceptible to devitrification.

34. **(Withdrawn)** The method of Claim 32, wherein coating at least a portion of said thermocouple sheath includes covering a tip of said thermocouple sheath.

35. **(Withdrawn)** The method of Claim 32, wherein coating at least a portion of said thermocouple includes covering a portion of the thermocouple that is near a susceptor of said chemical vapor deposition process chamber.

36. **(Withdrawn)** The method of Claim 25, wherein coating at least a portion of said one or more vitreous components includes coating an entire portion of a thermocouple sheath.

37. **(Withdrawn)** A chemical vapor deposition apparatus comprising a thermocouple, said thermocouple comprising thermocouple wires; a vitreous sheath surrounding the wires; and means for minimizing devitrification in said thermocouple.

38. **(Withdrawn)** The apparatus of Claim 37, wherein said means comprises a silicon nitride coating.

39. **(Withdrawn)** A support device configured to support a susceptor in a chemical vapor deposition chamber, said support device including a plurality of arms, each of said arms having a distal end configured to directly contact and support said susceptor, said distal end being covered at least in part by a devitrification barrier coating.

40. **(Withdrawn)** The support device of Claim 39, wherein said support device includes three arms.

41. **(Withdrawn)** The support device of Claim 39, wherein said distal end comprises an upwardly extending projection.

42. **(Withdrawn)** The support device of Claim 39, wherein said distal end is formed from quartz.

43. **(Withdrawn)** The support device of Claim 39, wherein said devitrification barrier coating comprises silicon nitride.

44. **(Withdrawn)** The support device of Claim 39, where said devitrification barrier coating is formed from the group consisting silicon nitride, diamond, titanium nitride, titanium carbon nitride and combinations thereof.

45. **(Withdrawn)** The support device of Claim 39, wherein said devitrification barrier coating covers an entire portion of said distal end.

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46. **(Previously presented)** The apparatus as in Claim 1, wherein said devitrification barrier coating is formed from silicon nitride that has been deposited on said one or more vitreous components using sputtering.

47. **(Previously presented)** The apparatus of Claim 1, wherein said devitrification barrier coating is formed by CVD.

48. **(Previously presented)** The apparatus of Claim 1, wherein said devitrification barrier coating is formed by sputtering.

46. **(Withdrawn)** The apparatus as in Claim 1, wherein said devitrification barrier coating is formed from silicon nitride that has been deposited on said one or more vitreous components using sputtering.

47. **(Withdrawn)** The apparatus of Claim 1, wherein said devitrification barrier coating is formed by CVD deposition.

48. **(Withdrawn)** The apparatus of Claim 1, wherein said devitrification barrier coating is formed by sputtering.

49. **(Withdrawn)** The apparatus of Claim 15, wherein said devitrification barrier coating is formed by CVD deposition.

50. **(Withdrawn)** The apparatus of Claim 15, wherein said devitrification barrier coating is formed by sputtering.

51. **(Withdrawn)** The method of Claim 25, wherein coating at least a portion of said one or more vitreous components with a barrier layer includes using sputtering to form said barrier layer.

52. **(Withdrawn)** The method of Claim 27, wherein said step of forming the barrier layer out of silicon nitride includes using sputtering to form said barrier layer.

53. **(Withdrawn)** The support device of Claim 39, wherein said devitrification barrier coating is formed by CVD deposition.

54. **(Withdrawn)** The support device of Claim 39, wherein said devitrification barrier coating is formed by sputtering.

55. **(Previously presented)** A semiconductor processing apparatus comprising a reaction chamber and a thermocouple, the thermocouple comprising a quartz sheath having an outer surface that is covered at least in part by a devitrification barrier coating having a thickness between about 1 and 10,000 angstroms.

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56. **(Previously presented)** The apparatus of Claim 55, wherein said devitrification barrier comprises silicon nitride.

57. **(Previously presented)** The apparatus of Claim 55, wherein said devitrification barrier coating is formed from silicon nitride that has been deposited on said thermocouple using CVD deposition.

58. **(Previously presented)** The apparatus of Claim 58, where said devitrification barrier coating has a thickness between about 50 and 5,000 angstroms.

59. **(Previously presented)** The apparatus of Claim 59, where said devitrification barrier coating has a thickness between about 500 and 3,000 angstroms.

60. **(Previously presented)** The apparatus of Claim 60, where said devitrification barrier coating has a thickness of about 800 angstroms.

61. **(Previously presented)** The apparatus of Claim 55, where said devitrification barrier coating is selected from the group consisting of silicon nitride, diamond, titanium nitride, titanium carbon nitride, and combinations thereof.

62. **(Previously presented)** The apparatus of Claim 55, wherein said devitrification barrier coating only covers a portion of said quartz sheath that is most susceptible to devitrification.

63. **(Previously presented)** The apparatus as in Claim 55, wherein said devitrification barrier coating is formed from silicon nitride that has been deposited on said thermocouple using sputtering.

64. **(Previously presented)** The apparatus of Claim 55, wherein said devitrification barrier coating is formed by CVD.

65. **(Previously presented)** The apparatus of Claim 55, wherein said devitrification barrier coating is formed by sputtering.